# NSN 5962-01-349-2196

Memory Microcircuit - Page 1 of 1



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# Storage Tempurature Range:

-65.0/+150.0 degrees celsius

### **Features Provided:**

Hermetically sealed and monolithic and programmable and radiation hardened

## **Inclosure Material:**

Ceramic

## Inclosure Configuration:

Dual-in-line

#### **Output Logic Form:**

Transistor-transistor logic

#### **Input Circuit Pattern:**

14 input

### Criticality Code Justification:

Feat

#### Current Rating Per Characteristic:

100.00 milliamperes reverse current, dc absolute

#### **Terminal Surface Treatment:**

Solder

## **Product Name:**

And gate array

## Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 7.0 volts power source

## **Time Rating Per Chacteristic:**

40.00 nanoseconds propagation delay

#### Memory Device Type:

Pal

#### **Special Features:**

Nuclear hardness critical item

## Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

## Terminal Type And Quantity:

24 printed circuit

#### Shelf Life:

N/a

# Unit Of Measure:

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# Demilitarization:

Yes - demil/mli

Fiig:

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